Product data sheet

1. General description

NPN/NPN matched double transistor in a very small SOT363 (TSSOP6) Surface-Mounted Device (SMD) plastic package. The transistors are fully isolated internally.

2. Features and benefits

- Current gain matching
- Base-emitter voltage matching
- Drop-in replacement for standard double transistors
- AEC-Q101 qualified

3. Applications

- Current mirror
- Differential amplifier

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
V _{CEO}	collector-emitter voltage	open base		-	-	65	V		
I _C	collector current			-	-	100	mA		
Per transistor							•		
h _{FE}	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		200	290	450			
Per device	Per device								
h _{FE1} /h _{FE2}	h _{FE} matching	V_{CE} = 5 V; I_{C} = 2 mA; T_{amb} = 25 °C		0.9	1	-			
V _{BE1} -V _{BE2}	V _{BE} matching		[2]	-	-	2	mV		

- [1] The smaller of the two values is taken as numerator.
- [2] The smaller of the two values is subtracted from the larger value.



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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	E	emitter TR1	654	6 5 4	
2	В	base TR1		P = 200	
3	С	collector TR2		0	TR1 TR2
4	E	emitter TR2			
5	В	base TR2	TSSOP6 (SOT363)	1 2 3	
6	С	collector TR1		sym020	

6. Ordering information

Table 3. Ordering information

Type number	Package	Je				
	Name	Description	Version			
BCM846BS	TSSOP6	plastic surface-mounted package; 6 leads	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code [1]
BCM846BS	F2%

[1] % = placeholder for manufacturing site code

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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transis	tor	'	1			
V _{CBO}	collector-base voltage	open emitter		-	80	V
V _{CEO}	collector-emitter voltage	open base		-	65	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
I _C	collector current			-	100	mA
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	200	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit		
Per transistor	Per transistor								
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W		
Per device									
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	-	416	K/W		

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transi	stor						
I _{CBO}	collector-base cut-off	V _{CB} = 30 V; I _E = 0 A; T _{amb} = 25 °C		-	-	15	nA
	current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C		-	-	5	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C		-	-	100	nA
h _{FE}	DC current gain	V_{CE} = 5 V; I_{C} = 2 mA; T_{amb} = 25 °C		200	290	450	
		V _{CE} = 5 V; I _C = 10 μA; T _{amb} = 25 °C		-	250	-	
V _{CEsat}	collector-emitter	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C		-	50	200	mV
saturation voltage	saturation voltage	I_C = 100 mA; I_B = 5 mA; pulsed;		-	200	400	mV
V _{BEsat}	base-emitter saturation	$t_p \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C$	[1]	-	910	-	mV
	voltage	I_C = 10 mA; I_B = 0.5 mA; T_{amb} = 25 °C	[1]	-	760	-	mV
V_{BE}	base-emitter voltage	V_{CE} = 5 V; I_{C} = 10 mA; T_{amb} = 25 °C	[2]	-	-	770	mV
V_{BE}	base-emitter voltage	V_{CE} = 5 V; I_{C} = 2 mA; T_{amb} = 25 °C	[2]	610	660	710	mV
C _C	collector capacitance	V _{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C		-	-	1.5	pF
C _E	emitter capacitance	$V_{EB} = 0.5 \text{ V}; I_{C} = 0 \text{ A}; i_{c} = 0 \text{ A};$ $f = 1 \text{ MHz}; T_{amb} = 25 ^{\circ}\text{C}$		-	11	-	pF
f _T	transition frequency	V_{CE} = 5 V; I_{C} = 10 mA; f = 100 MHz; T_{amb} = 25 °C		100	250	-	MH
NF	noise figure	V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; f = 1 kHz; B = 200 Hz; T_{amb} = 25 °C		-	3.3	-	dB
		V_{CE} = 5 V; I_{C} = 0.2 mA; R_{S} = 2 k Ω ; T_{amb} = 25 °C; f = 10 Hz to 15.7 kHz		-	2.8	-	dB
Per device	e		1	1	1	1	
h _{FE1} /h _{FE2}	h _{FE} matching	V_{CE} = 5 V; I_{C} = 2 mA; T_{amb} = 25 °C	[3]	0.9	1	-	
V _{BE1} -V _{BE2}	V _{BE} matching		[4]	-	-	2	mV

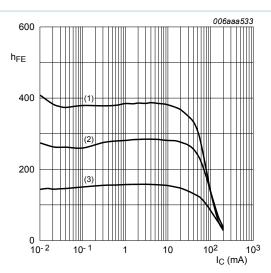
^[1] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[2] V_{BE} decreases by about 2 mV/K with increasing temperature.

^[3] The smaller of the two values is taken as numerator.

^[4] The smaller of the two values is subtracted from the larger value.

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$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

$$(3) T_{amb} = -55 °C$$

Fig. 1. DC current gain as a function of collector current; typical values

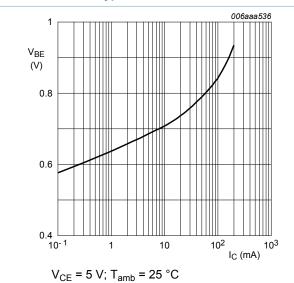


Fig. 3. Base-emitter voltage as a function of collector current; typical values

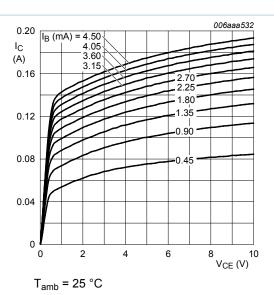
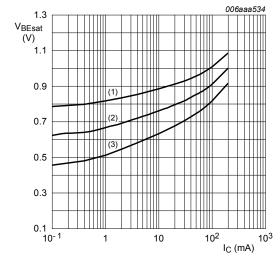


Fig. 2. Collector current as a function of collectoremitter voltage; typical values



 $I_{\rm C}/I_{\rm B} = 20$

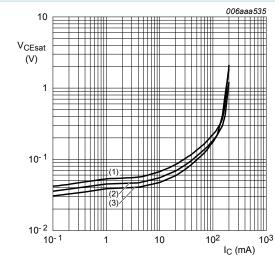
(1) $T_{amb} = -55 \, ^{\circ}C$

(2) T_{amb} = 25 °C

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 4. Base-emitter saturation voltage as a function of collector current; typical values

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$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig. 5. Collector-emitter saturation voltage as a function of collector current; typical values

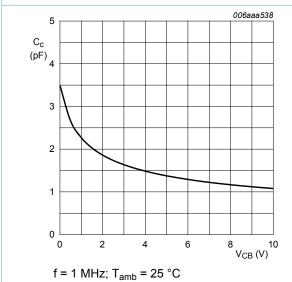
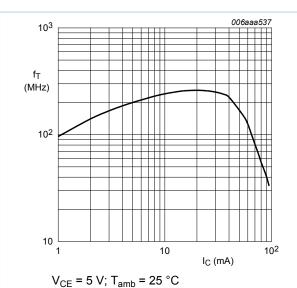
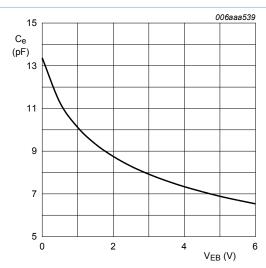


Fig. 7. Collector capacitance as a function of collector-base voltage; typical values



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Fig. 6. Transition frequency as a function of collector current; typical values

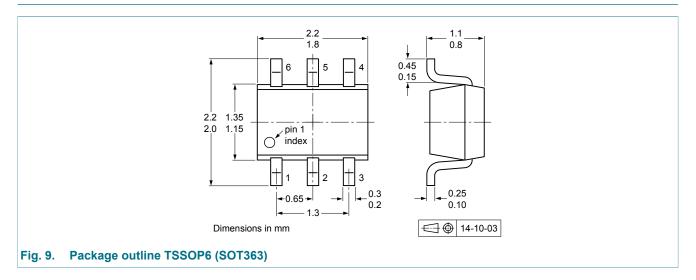


f = 1 MHz; T_{amb} = 25 °C

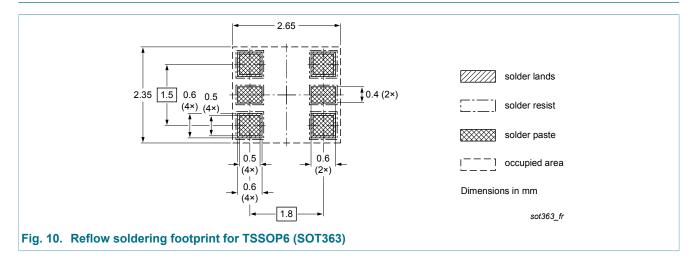
Emitter capacitance as a function of emitterbase voltage; typical values

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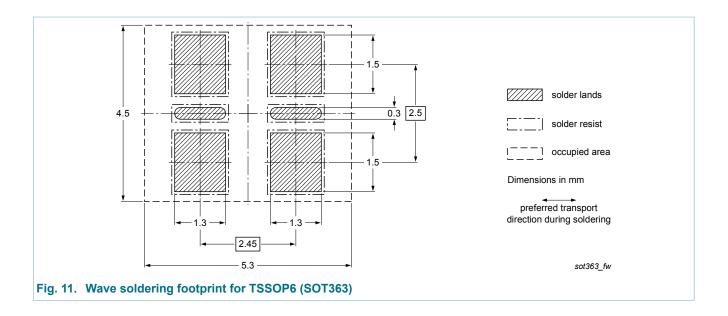
11. Package outline



12. Soldering



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13. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status Change notice		Supersedes		
BCM846BS v.2	20150626	Product data sheet	-	BCM846BS v.1		
Modification:	Product status changed					
BCM846BS v.1	20150424	Objective data sheet	-	-		

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14. Legal information

14.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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